

AMENDMENTS TO THE CLAIMS

Please amend the Claims as follows:

1 – 6. (Canceled)

7. (Currently Amended) A light emitting diode comprising a pellet, a major front surface of which, where an electrode is formed, is made of a GaAsP mixed crystal, characterized in that the major front surface is a rough surface; and characterized in that all side surfaces of the pellet are rough surfaces, wherein the rough surfaces are formed with fine projections with convex surfaces, the fine projections being arc-like sectional shapes to be formed densely by wet-etching the pellet, and wherein each of the fine projections has a diameter in a range of 0.3 μm to less than 3 μm , and the diameter is a length from a foot of one of the fine projections to a foot of next one of the fine projections, and wherein the convex surfaces of the rough surfaces are configured to allow a light getting to an interface between a light emitting surface and the air at an angle larger than a critical angle of total reflection θ to be transited into the air through the convex surfaces.

8 – 10. (Canceled)

11. (Currently Amended) A fabrication process for a light emitting diode having, comprising forming a pellet on, a major front surface of a light emitting diode dice ~~which~~, where an electrode is formed, wherein the major front surface is made of a GaAsP mixed crystal, ~~characterized in that~~ wet-etching the pellet ~~is treated with an etching solution of an aqueous solution~~ selected from a groups consisting of ~~containing~~ Br_2 , nitric

acid, hydrofluoric acid and acetic acid and or I₂, nitric acid, hydrofluoric acid, and acetic acid to form fine projections that are ~~are like sectional shapes to be~~ formed densely on the major front surface and all side surfaces of the pellet, wherein the fine projections have a diameter in a range of 0.3 μm to less than 3 μm and the diameter is a length from a foot of one of the fine projections to a foot of next one of the fine projections.

12. (Canceled)

13. (Previously Presented) A fabrication process for a light emitting diode according to claim 11, characterized in that the etching solution contains 40 to 80 parts of nitric acid, 40 to 300 parts of hydrofluoric acid and 400 to 2000 parts of acetic acid based on 1 part of Br₂ or I₂ in a molar ratio.

14. (Canceled)